Ordering number : ENA1085

SANYO Semiconductors
DATA SHEET

2SA1965-S — PNP Epitaxial Planar Silicon Transistor
Muting Circuit Applications

Features

- Ultrasmall-sized package permitting applied sets to be made small and slim.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Low ON resistance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		–15	V
Collector-to-Emitter Voltage	V_{CEO}		–10	V
Emitter-to-Base Voltage	V_{EBO}		–5	V
Collector Current	I_C		–100	mA
Collector Current (Pulse)	I_{CP}		–200	mA
Base Current	I_B		–20	mA
Collector Dissipation	P_C		150	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=–12V, I_E=0A			–0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–4V, I_C=0A			–0.1	μA
DC Current Gain	h_{FE}	V_{CE}=–2V, I_C=–5mA	200		600	
Gain-Bandwidth Product	f_T	V_{CE}=–5V, I_C=–10mA		600		MHz
Output Capacitance	Cob	V_{CB}=–10V, f=1MHz		5.0		pF

Marking : KA

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=–10mA, I_B=–1mA		–16	–35	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=–10mA, I_B=–1mA		–0.75	–1.1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0A	–15			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–10			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=–10μA, I_C=0A	–5			V
On Resistance	Ron	I_B=–3mA, f=1MHz		1.2		Ω

Package Dimensions

unit : mm (typ)

7029-002